

Abstract of the Disclosure:

A method for fabricating a semiconductor component is based on a nitride compound semiconductor. In a first step of the method, provision is made of a semiconductor body containing
5 at least one nitride compound semiconductor. In a second step, a metal layer is applied to the surface of the semiconductor body. Afterward, in a third step, the semiconductor body is patterned, a part of the metal layer and parts of the underlying semiconductor body are removed.

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